

SN65LBC175、SN75LBC175 四通道低功耗差分线路接收器

1 特性

- 符合或超出 EIA 标准 RS-422-A、RS-423-A、RS-485 和 CCITT 建议 V.11
- 可以低至 20ns 的脉冲持续时间运行
- 适用于嘈杂环境中长总线上的多点传输
- 输入灵敏度： $\pm 200\text{mV}$
- 低功耗：20 mA (最大值)
- 开路失效防护设计
- 7 V 至 12V 的共模输入电压范围
- 与 SN75175 和 LTC489 引脚兼容

2 应用

- 工厂自动化
- ATM 和点钞机
- 智能电网
- 交流和伺服电机驱动器

3 说明

SN65LBC175 和 SN75LBC175 是具有三态输出的单片四通道差分线路接收器，旨在满足 EIA 标准 RS-422-A、RS-423-A、RS-485 和 CCITT 建议 V.11 的要求。这个器件针对数据速率高达和超过每秒 10 兆位的平衡多点总线传输进行了优化。接收器采用高电平

有效使能输入成对启用。每个差分接收器都输入具有高阻抗、用于提高抗噪性的迟滞，以及在 -12V 至 -7V 共模输入电压范围内 $\pm 200\text{mV}$ 的灵敏度。失效防护设计可确保在输入处于开路状态时，输出始终处于高电平状态。这两款器件都采用 TI 专有 LinBiCMOS™ 技术进行设计，可实现低功耗、高开关速度和稳健性。

这些器件会在与 SN75LBC172 或 SN75LBC174 四通道线路驱动器配合使用时提供卓越性能。SN65LBC175 采用 16 引脚 DIP (N)、小外形封装 (D) 和宽外形封装 (DW)。SN75LBC175 采用 16 引脚 DIP (N) 和小外形封装 (D)。

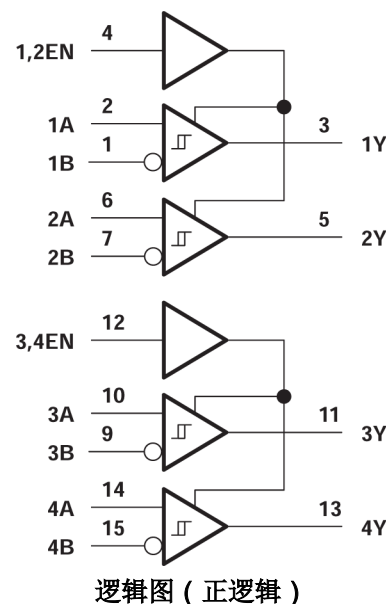
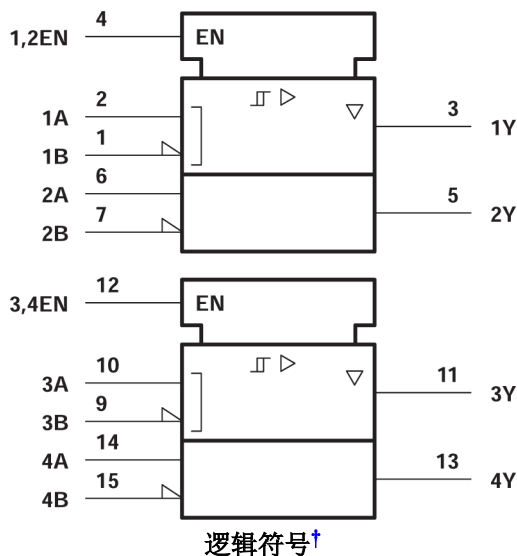
SN65LBC175 可在 -40°C 至 85°C 的工业温度范围内运行。SN75LBC175 可在 0°C 至 70°C 的商用温度范围内运行。

封装信息

器件型号	封装 ⁽¹⁾	封装尺寸 ⁽²⁾
SN65LBC175 SN75LBC175	D (SOIC, 16)	9.9mm × 6mm
	DW (SOIC, 16)	10.3mm × 10.3mm
	N (PDIP, 16)	19.3mm × 9.4mm

(1) 有关详细信息，请参阅节 10。

(2) 封装尺寸 (长 × 宽) 为标称值，并包括引脚 (如适用)。



† 此符号符合 ANSI/IEEE 标准 91-1984 和 IEC 出版物 617-12。



Table of Contents

1 特性	1	6 Parameter Measurement Information	9
2 应用	1	7 Detailed Description	11
3 说明	1	7.1 Device Functional Modes.....	11
4 Pin Configuration and Functions	3	8 Device and Documentation Support	12
5 Specifications	4	8.1 接收文档更新通知.....	12
5.1 Absolute Maximum Ratings.....	4	8.2 支持资源.....	12
5.2 ESD Ratings.....	4	8.3 Trademarks.....	12
5.3 Dissipation Rating Table.....	4	8.4 静电放电警告.....	12
5.4 Thermal Information.....	5	8.5 术语表.....	12
5.5 Recommended Operating Conditions.....	5	9 Revision History	12
5.6 Electrical Characteristics.....	6	10 Mechanical, Packaging, and Orderable	
5.7 Switching Characteristics.....	6	Information	12
5.8 Typical Characteristics.....	7		

4 Pin Configuration and Functions

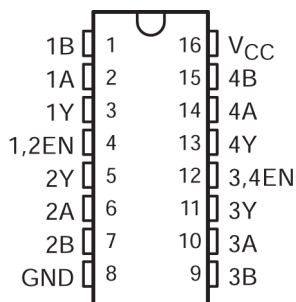


图 4-1. D, DW, or N Package (Top View)

表 4-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1B	1	I	Channel 1 Inverting Differential Input
1A	2	I	Channel 1 Non-Inverting Differential Input
1Y	3	O	Channel 1 Output
1,2 EN	4	I	Channel 1 and 2 Active High Enable
2Y	5	O	Channel 2 Output
2A	6	I	Channel 2 Non-Inverting Differential Input
2B	7	I	Channel 2 Inverting Differential Input
GND	8	GND	Device Ground
3B	9	I	Channel 3 Inverting Differential Input
3A	10	I	Channel 3 Non-Inverting Differential Input
3Y	11	O	Channel 3 Output
3,4 EN	12	I	Channel 3 and 4 Active High Enable
4Y	13	O	Channel 4 Output
4A	14	I	Channel 4 Non-Inverting Differential Input
4B	15	I	Channel 4 Inverting Differential Input
V _{CC}	16	POW	Device Supply

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CC} (see ⁽²⁾)	Supply voltage range		-0.3	7	V
V_I	Input voltage	(A or B inputs)		± 25	V
V_{ID} (see ⁽³⁾)	Differential input voltage			± 25	V
	Voltage range at Y, 1/2EN, 3/4EN		-0.3	$V_{CC} + 0.5$	V
	Continuous total dissipation		See Dissipation Rating Table		
T_A	Operating free-air temperature range:	SN65LBC175	-40	85	°C
		SN75LBC175	0	70	°C
T_{stg}	Storage temperature range		-65	150	°C

- (1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to GND.
- (3) Differential input voltage is measured at the noninverting input with respect to the corresponding inverting input.

5.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	± 1000
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	± 1500
		Machine Model (MM)	± 200

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

over operating free-air temperature range (unless otherwise noted)

5.3 Dissipation Rating Table

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING
D	1100 mW	8.7 mW/°C	709 mW	578 mW
DW	1200 mW	9.6 mW/°C	770 mW	625 mW
N	1150 mW	9.2 mW/°C	736 mW	598 mW

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SOIC (D)	SOIC (DW)	PDIP (N)	UNIT
		16 Pins	16 Pins	16 Pins	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	84.6	71.1	60.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	43.5	37.4	48.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.2	36.8	40.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	10.4	13.3	27.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	42.8	36.4	40.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

5.5 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT	
Supply voltage, V _{CC}		4.75	5	5.25	V	
Common-mode input voltage, V _{IC}		-7			12	V
Differential input voltage, V _{ID}					±6	V
High-level input voltage, V _{IH}	EN inputs	2				V
Low-level input voltage, V _{IL}					0.8	V
High-level output current, I _{OH}					-8	mA
Low-level output current, I _{OL}					8	mA
Operating free-air temperature, T _A	SN65LBC175	-40			85	°C
	SN75LBC175	0			70	

5.6 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER			TEST CONDITIONS			MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IT+}	Positive-going input threshold voltage		I _O = -8 mA			0.2			V
V _{IT-}	Negative-going input threshold voltage		I _O = 8 mA			-0.2			V
V _{hys}	Hysteresis voltage (V _{IT+} - V _{IT-})						45		mV
V _{IK}	Enable input clamp voltage		I _I = -18 mA				-0.9	-1.5	V
V _{OH}	High-level output voltage		V _{ID} = 200 mV,	I _{OH} = -8 mA		3.5	4.5		V
V _{OL}	Low-level output voltage		V _{ID} = -200 mV,	I _{OL} = 8 mA			0.3	0.5	V
I _{OZ}	High-impedance-state output current		V _O = 0 V to V _{CC}					±20	μA
I _I	Bus input current	A or B inputs	V _{IH} = 12 V,	V _{CC} = 5 V,	Other inputs at 0 V	0.7		1	mA
			V _{IH} = 12 V,	V _{CC} = 0 V,	Other inputs at 0 V	0.8		1	
			V _{IH} = -7 V,	V _{CC} = 5 V,	Other inputs at 0 V	-0.5		-0.8	
			V _{IH} = -7 V,	V _{CC} = 0 V,	Other inputs at 0 V	-0.4		-0.8	
I _{IH}	High-level enable input current		V _{IH} = 5 V					±20	μA
I _{IL}	Low-level enable input current		V _{IL} = 0 V					-20	μA
I _{OS}	Short-circuit output current		V _O = 0			-80		-120	mA
I _{CC}	Supply current		Outputs enabled,	I _O = 0,	V _{ID} = 5 V		11	20	mA
			Outputs disabled				0.9	1.4	

(1) All typical values are at $V_{CC} = 5 \text{ V}$ and $T_A = 25^\circ\text{C}$.

5.7 Switching Characteristics

$V_{CC} = 5 \text{ V}$, $C_L = 15 \text{ pF}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t_{PHL}	Propagation delay time, high- to low-level output	$V_{ID} = -1.5 \text{ V to } 1.5 \text{ V}$, See 图 6-1	11	22	30	ns
t_{PLH}	Propagation delay time, low- to high-level output		11	22	30	ns
t_{PZH}	Output enable time to high level	See 图 6-2	17		30	ns
t_{PZL}	Output enable time to low level	See 图 6-3	18		30	ns
t_{PHZ}	Output disable time from high level	See 图 6-2	30		40	ns
t_{PLZ}	Output disable time from low level	See 图 6-3	23		30	ns
$t_{sk(p)}$	Pulse skew ($ t_{PHL} - t_{PLH} $)	See 图 6-2	4		6	ns
t_t	Transition time	See 图 6-1	3		10	ns

5.8 Typical Characteristics

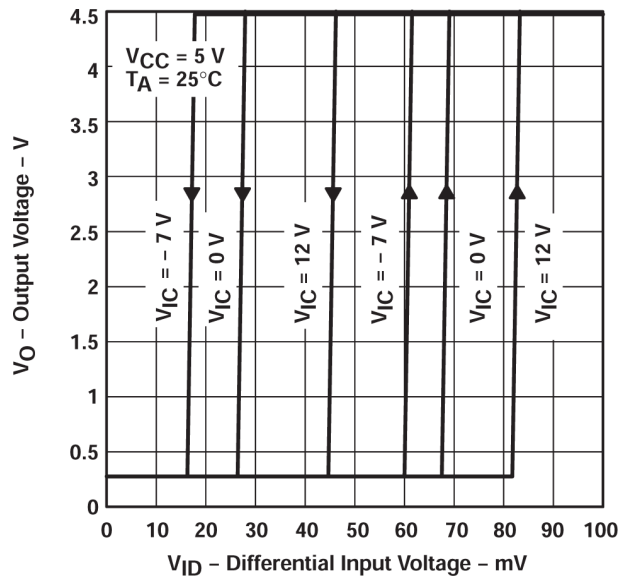


图 5-1. Output Voltage vs Differential Input Voltage

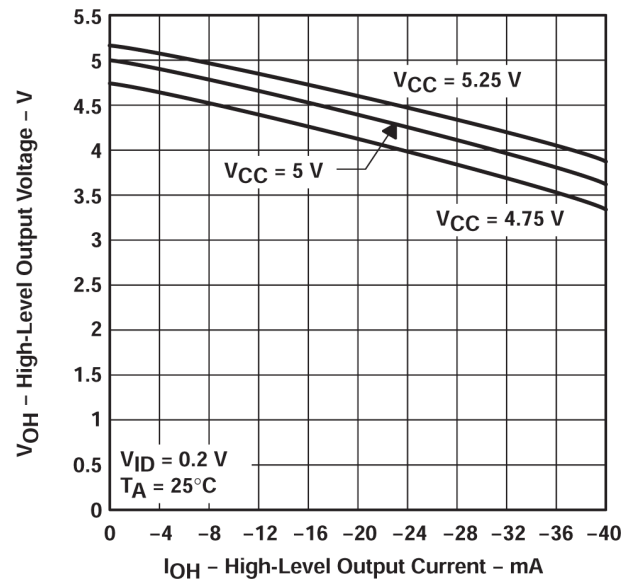


图 5-2. High-level Output Voltage vs High-level Output Current

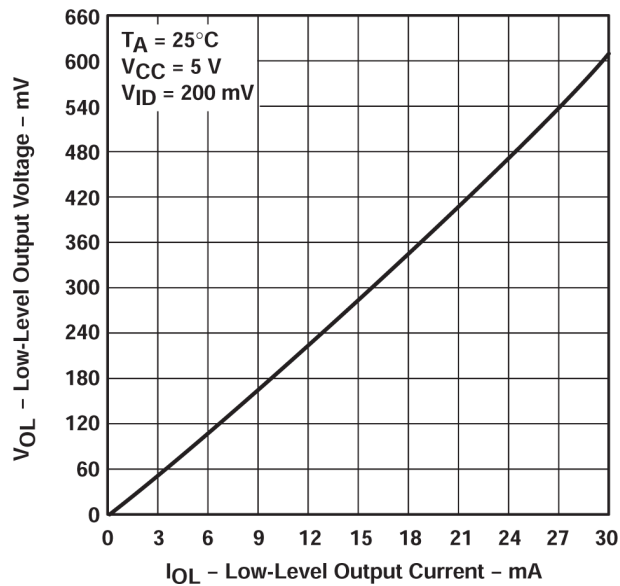


图 5-3. Low-level Output Voltage vs Low-level Output Current

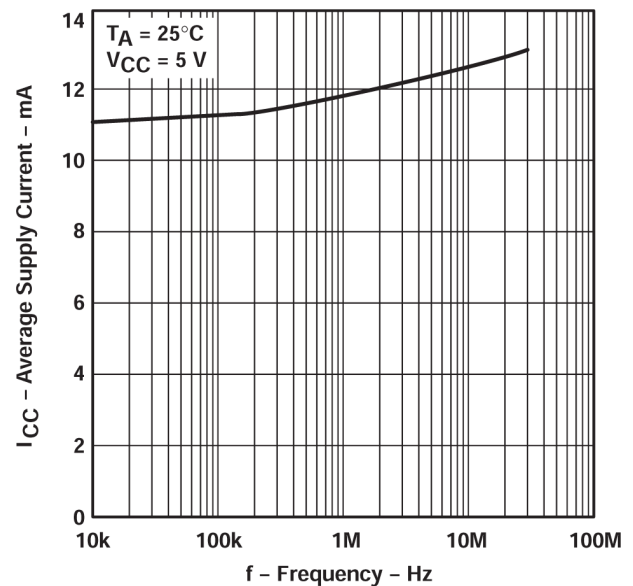


图 5-4. Average Supply Current vs Frequency

5.8 Typical Characteristics (continued)

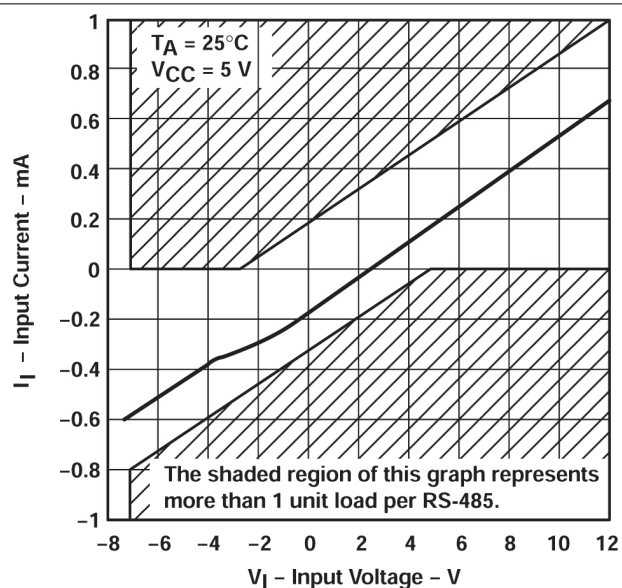


图 5-5. Input Current vs Input Voltage (Complementary Input at 0 v)

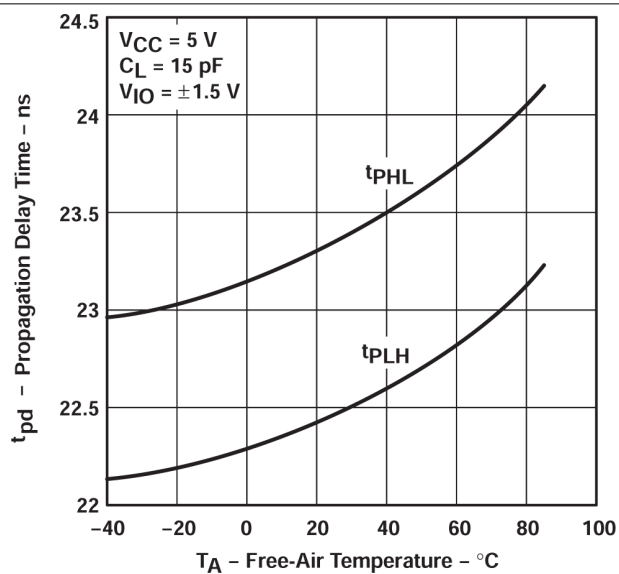


图 5-6. Propagation Delay Time vs Free-air Temperature

6 Parameter Measurement Information

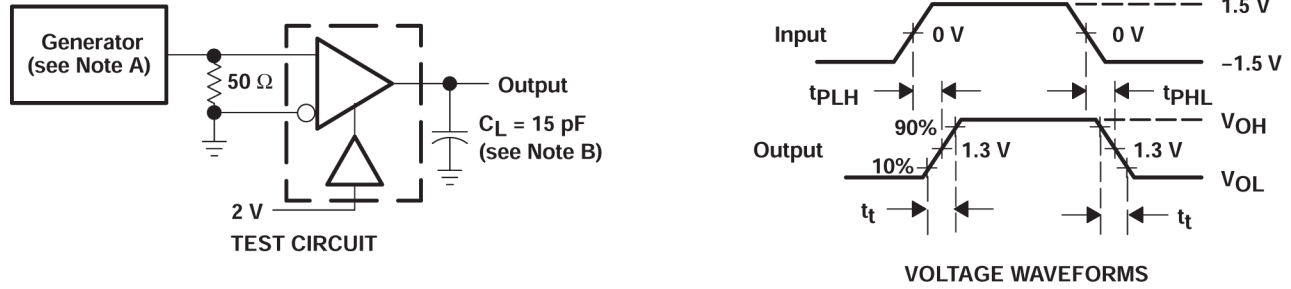
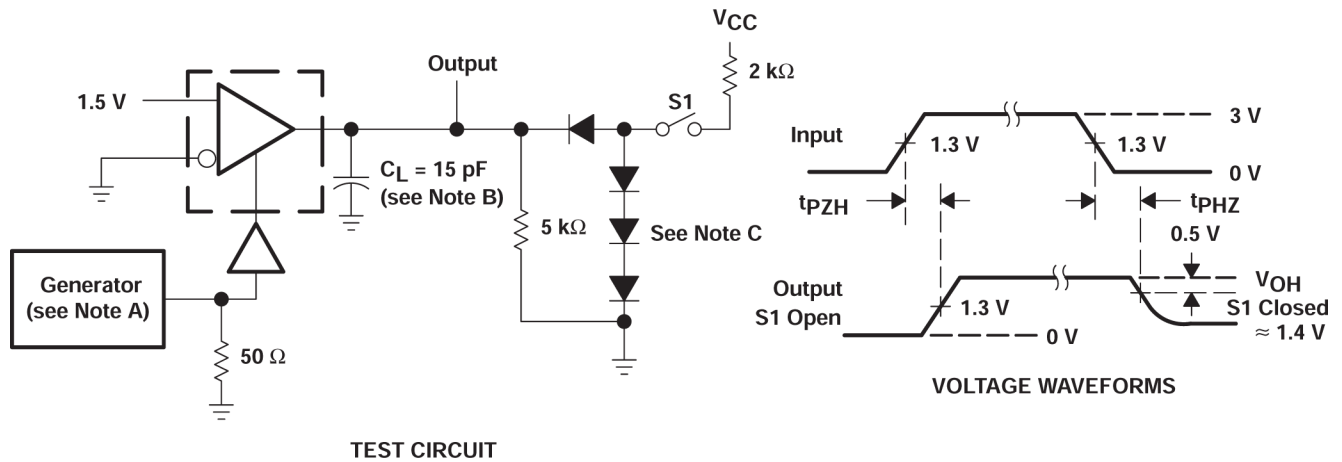
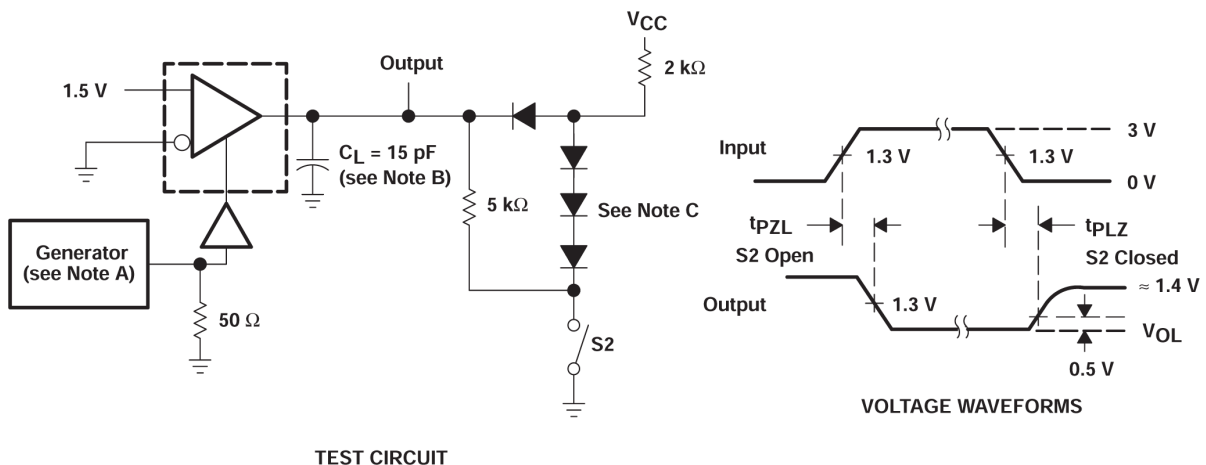


图 6-1. t_{PLH} and t_{PHL} Test Circuit and Voltage Waveforms



- A. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_r \leq 6$ ns, $t_f \leq 6$ ns, $Z_O = 50 \Omega$.
- B. C_L includes probe and jig capacitance.
- C. All diodes are 1N916 or equivalent.

图 6-2. t_{PHZ} and t_{PZH} Test Circuit and Voltage Waveforms



- A. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_r \leq 6$ ns, $t_f \leq 6$ ns, $Z_O = 50 \Omega$.
- B. C_L includes probe and jig capacitance.

C. All diodes are 1N916 or equivalent.

图 6-3. t_{PZL} and t_{PLZ} Test Circuit and Voltage Waveforms

7 Detailed Description

7.1 Device Functional Modes

表 7-1. Function Table (Each Receiver)

DIFFERENTIAL INPUTS	ENABLE ⁽¹⁾	OUTPUT
A-B		Y
$V_{ID} \geq 0.2 \text{ V}$	H	H
$-0.2 \text{ V} < V_{ID} < 0.2 \text{ V}$	H	?
$V_{ID} \leq -0.2 \text{ V}$	H	L
X	L	Z
Open circuit	H	H

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off), ? = indeterminate

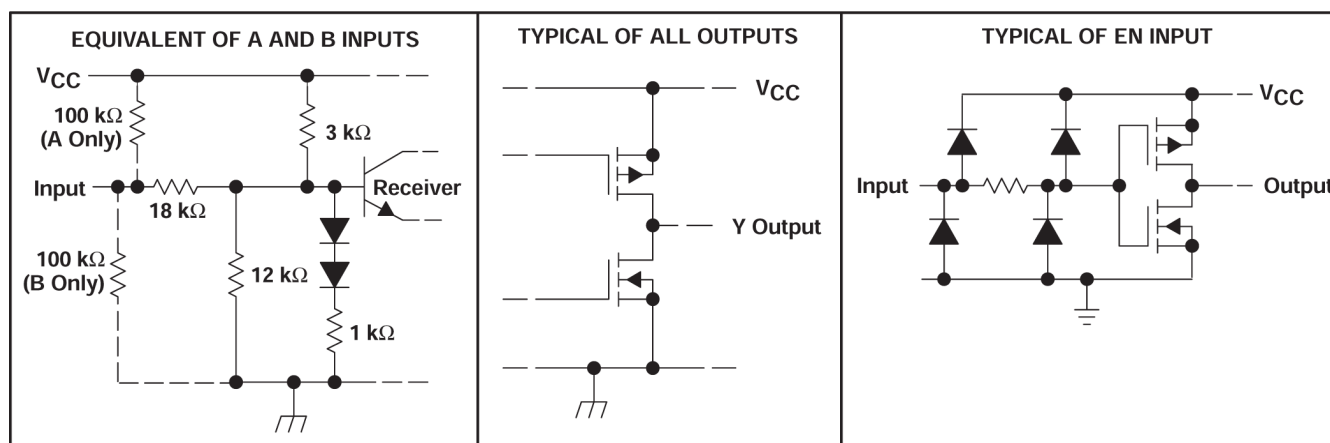


图 7-1. Schematics of Inputs and Outputs

8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

8.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

8.2 支持资源

[TI E2E™ 支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

8.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

8.4 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

8.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

9 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision G (March 2009) to Revision H (November 2023)	Page
• 更改了整个文档中的表格、图和交叉参考的编号格式.....	1

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65LBC175D	LIFEBUY	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65LBC175	
SN65LBC175DG4	LIFEBUY	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65LBC175	
SN65LBC175DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65LBC175	Samples
SN65LBC175DW	LIFEBUY	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65LBC175	
SN65LBC175DWG4	LIFEBUY	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65LBC175	
SN65LBC175DWR	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65LBC175	Samples
SN65LBC175N	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN65LBC175N	Samples
SN75LBC175D	LIFEBUY	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75LBC175	
SN75LBC175DR	LIFEBUY	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75LBC175	
SN75LBC175N	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	SN75LBC175N	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

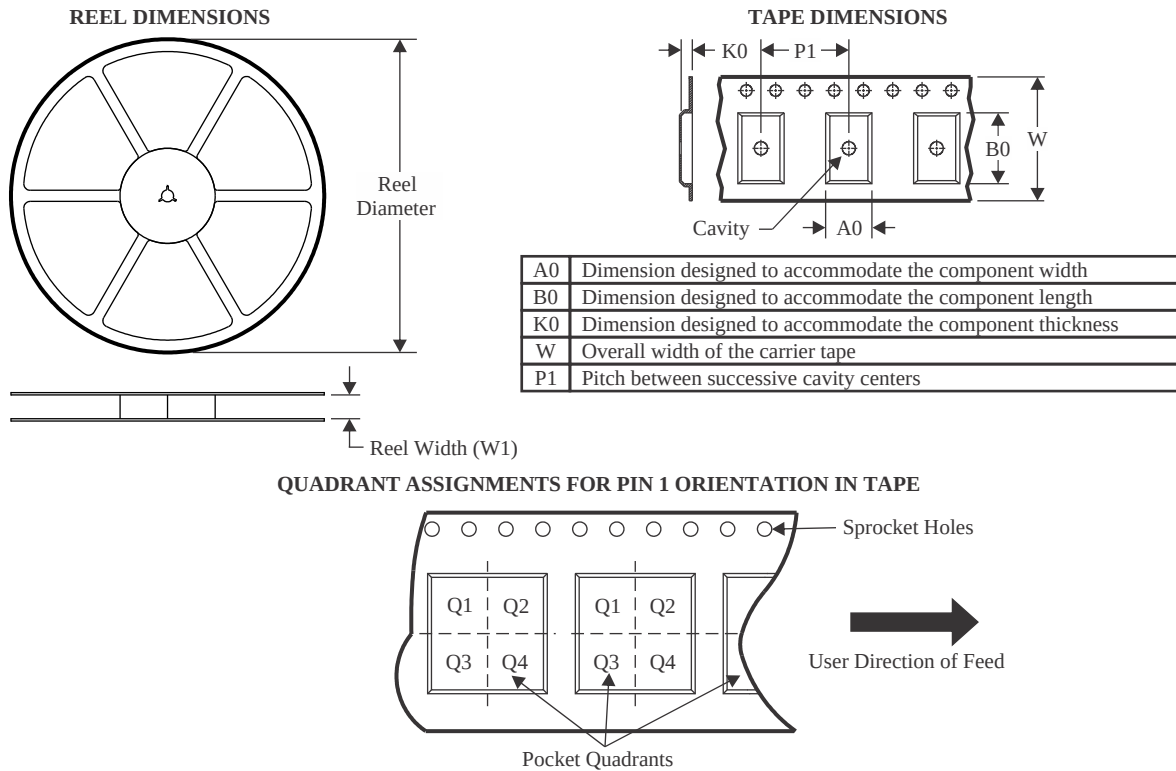
OTHER QUALIFIED VERSIONS OF SN75LBC175 :

- Military : [SN55LBC175](#)

NOTE: Qualified Version Definitions:

- Military - QML certified for Military and Defense Applications

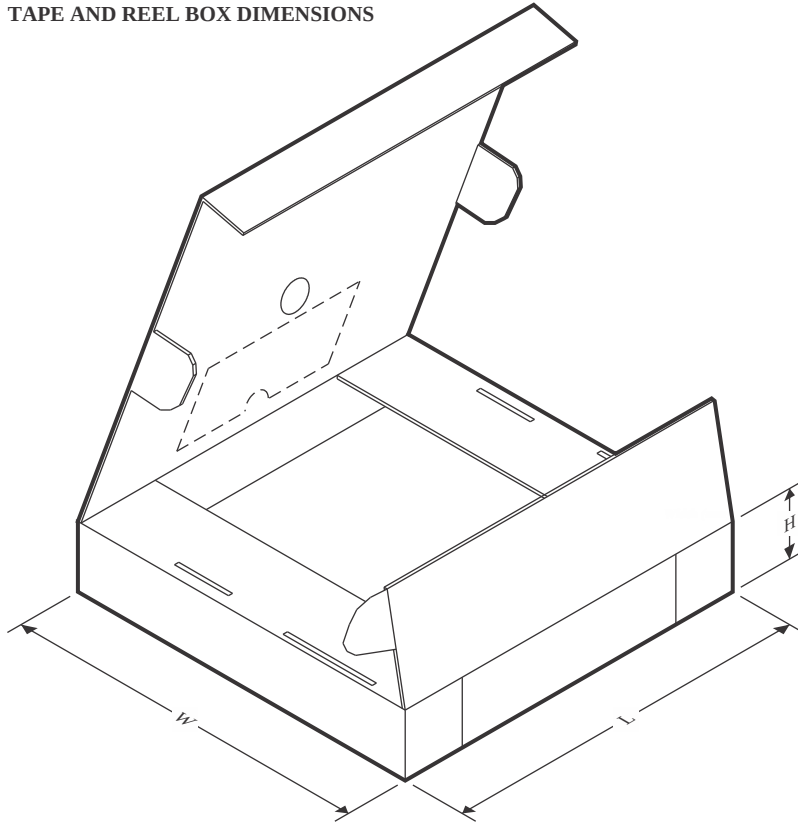
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LBC175DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65LBC175DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN75LBC175DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN75LBC175DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LBC175DR	SOIC	D	16	2500	353.0	353.0	32.0
SN65LBC175DWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN75LBC175DR	SOIC	D	16	2500	350.0	350.0	43.0
SN75LBC175DR	SOIC	D	16	2500	340.5	336.1	32.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65LBC175D	D	SOIC	16	40	505.46	6.76	3810	4
SN65LBC175D	D	SOIC	16	40	507	8	3940	4.32
SN65LBC175DG4	D	SOIC	16	40	507	8	3940	4.32
SN65LBC175DG4	D	SOIC	16	40	505.46	6.76	3810	4
SN65LBC175DW	DW	SOIC	16	40	506.98	12.7	4826	6.6
SN65LBC175DWG4	DW	SOIC	16	40	506.98	12.7	4826	6.6
SN65LBC175N	N	PDIP	16	25	506	13.97	11230	4.32
SN65LBC175N	N	PDIP	16	25	506	13.97	11230	4.32
SN75LBC175D	D	SOIC	16	40	505.46	6.76	3810	4
SN75LBC175D	D	SOIC	16	40	507	8	3940	4.32
SN75LBC175N	N	PDIP	16	25	506	13.97	11230	4.32

GENERIC PACKAGE VIEW

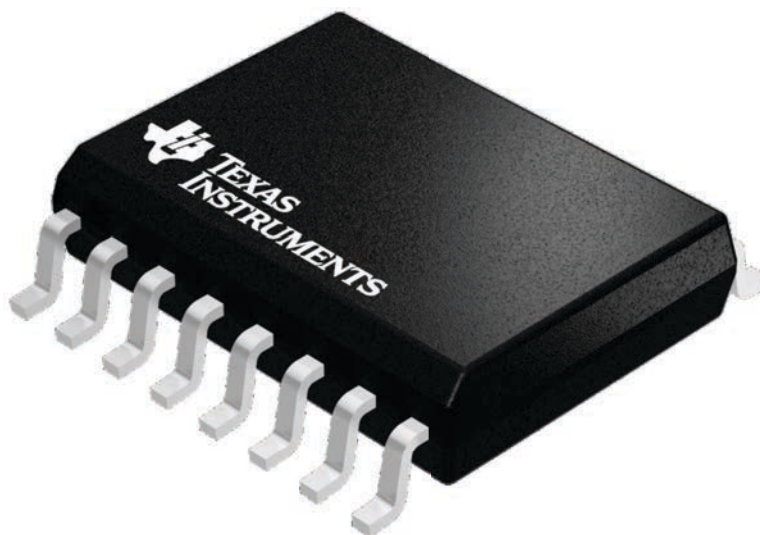
DW 16

SOIC - 2.65 mm max height

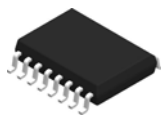
7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224780/A

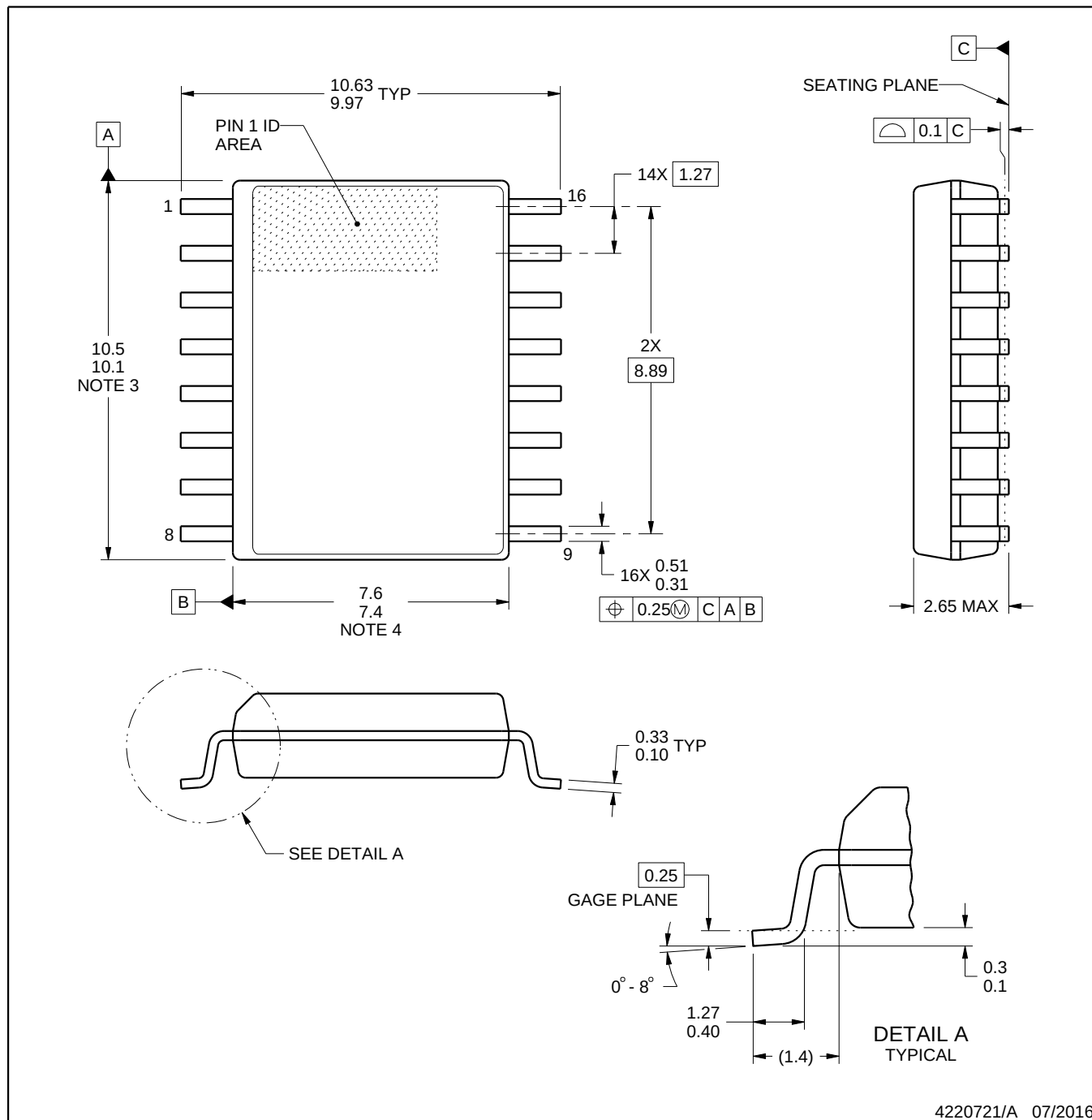


DW0016A

PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



4220721/A 07/2016

NOTES:

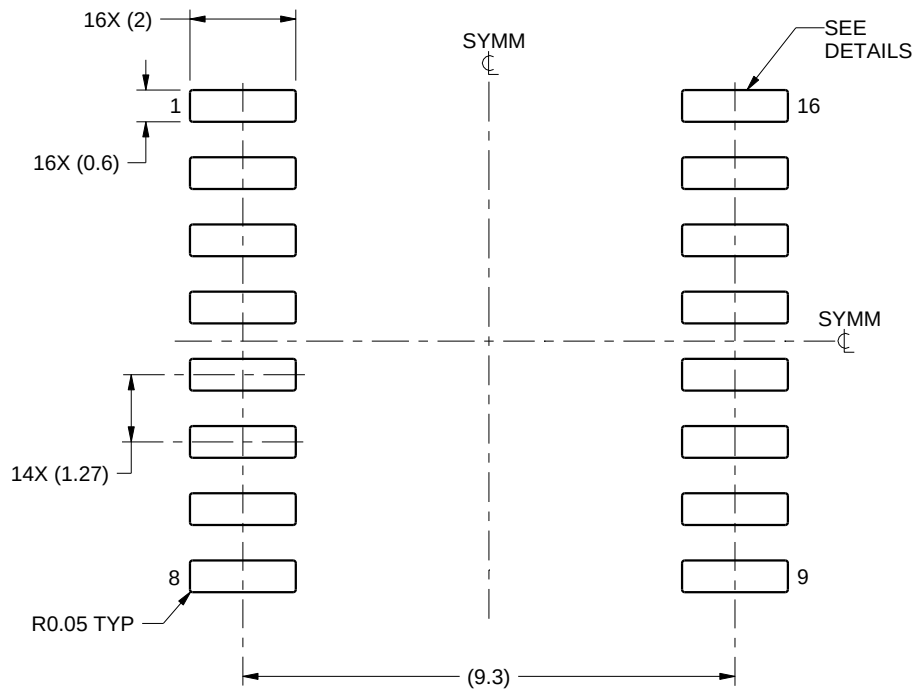
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

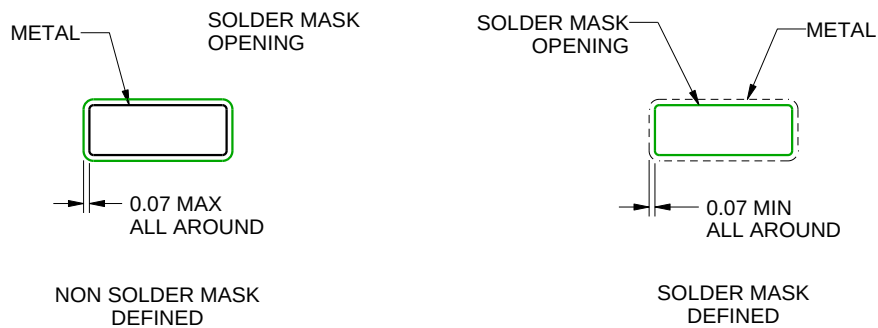
DW0016A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:7X



SOLDER MASK DETAILS

4220721/A 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

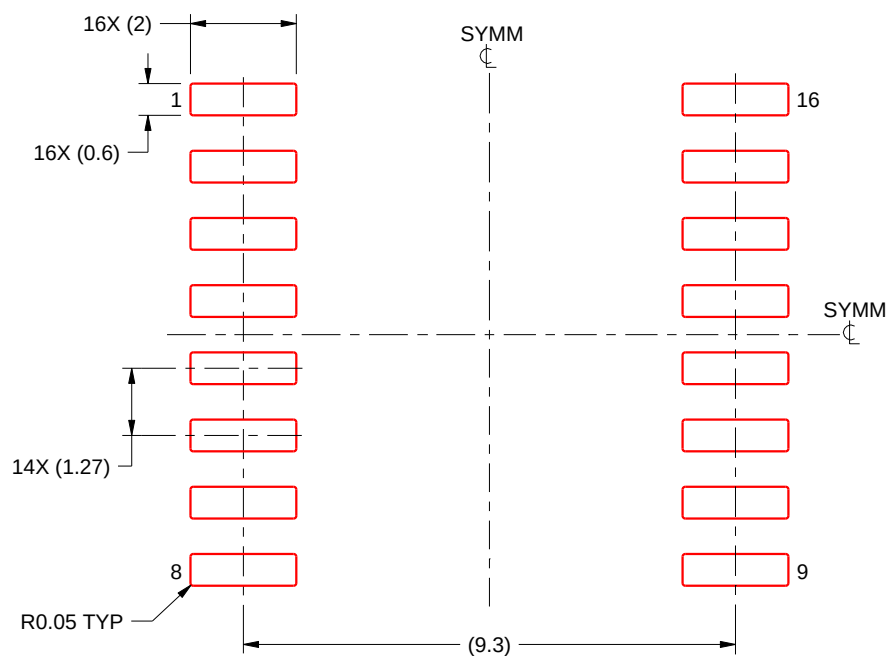
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0016A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:7X

4220721/A 07/2016

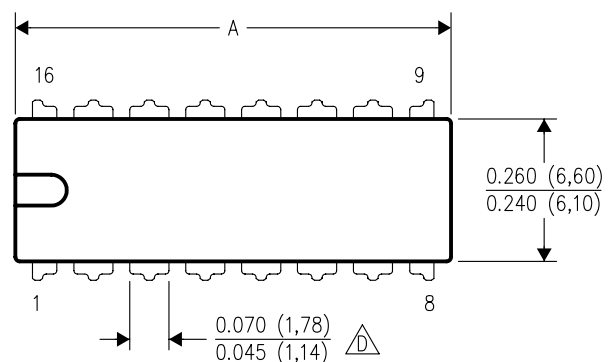
NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

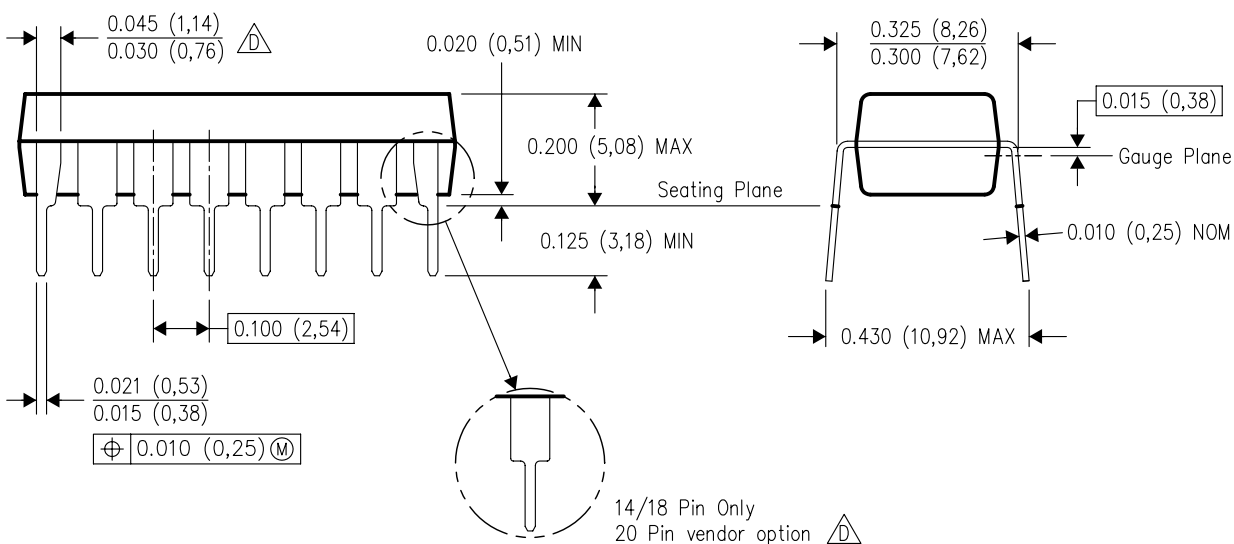
N (R-PDIP-T**)

16 PINS SHOWN

PLASTIC DUAL-IN-LINE PACKAGE



PINS ** DIM	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS-001 VARIATION	AA	BB	AC	AD

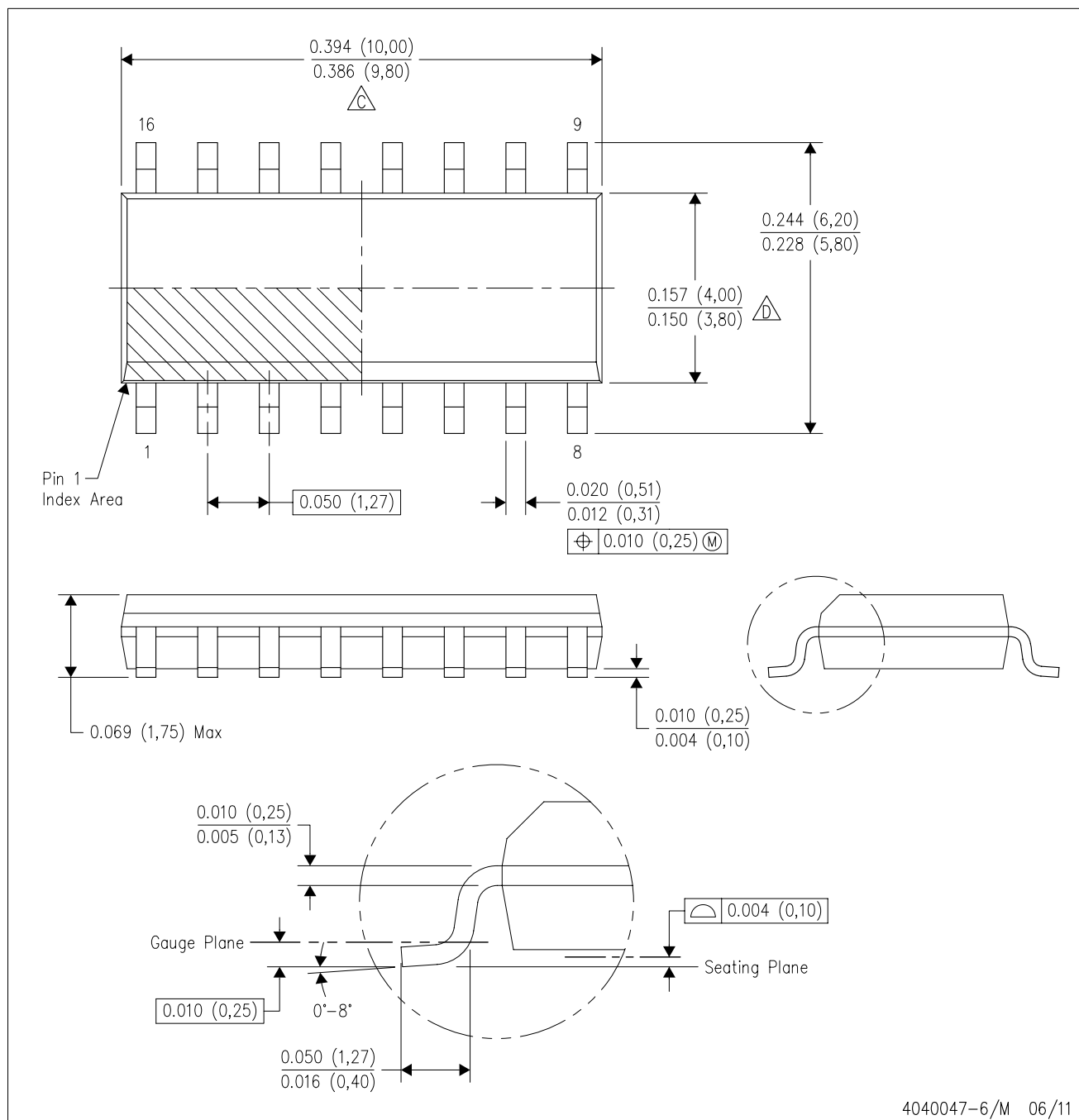


4040049/E 12/2002

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 -  Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 -  The 20 pin end lead shoulder width is a vendor option, either half or full width.

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



4040047-6/M 06/11

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AC.

重要声明和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 [TI 的销售条款](#) 或 [ti.com](#) 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2024，德州仪器 (TI) 公司